

Mono N-Type Silicon Wafer (10A8N)

182.3x188



Geometric Parameter

Side length Short Side:182.3±0.25mm,Long Side:188±0.25mm

Diagonal 256±0.25mm

Thickness 130(+8/-8)μm

Arc length projection 182 Length:4.27±0.5mm
188 Length:4.14±0.5mm

Electrical Properties

Resistivity 0.6-1.6Ω·cm

Minority carrier ≥1000μs

Oxygen content ≤5.75x10¹⁷at/cm³

Carbon content ≤5x10¹⁶at/cm³

Material Properties

Growth method CZ

Orientation <100>±2°

Surface Performance

TTV ≤20

Warpage ≤40

Line mark ≤13

Edge collapse Depth≤0.3mm, length≤0.5mm, no more than one places

Cracks and perforations Invisible by visual inspection

Silicon wafer surface Clean, free of oil, soap, glue and other residues